

**PATENT NUMBER and
ISSUE DATE**

U.S. UTILITY Patent Application

2

5/5/03

APPL NUM 10036303	FILING DATE 12/28/2001	CLASS 257	SUBCLASS 5	GAU 2811	EXAMINER S. D. [Signature]
**APPLICANTS: Hawley Frank; Wang Daniel;					
**CONTINUING DATA VERIFIED: THIS APPLICATION IS A DIV OF 09/741,949 12/20/2000					
** FOREIGN APPLICATIONS VERIFIED:					
PG-PUB	<input checked="" type="checkbox"/> DO NOT PUBLISH	RESCIND <input type="checkbox"/>			
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiner's initials			ATTORNEY DOCKET NO ACT-307DVA		
TITLE : Method for fabricating a MOS transistor having improved total radiation-induced leakage current					
U.S. DEPT. OF COMMERCE & TM-PTO-436L(Rev. 12-94)					

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NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	
ISSUE FEE		Total Claims Print Claim for O.G.	
Amount Due	Date Paid		
TERMINAL DISCLAIMER		DRAWING	
		Sheets Drwg.	Figs.Drwg.
		Print Fig.	
		Primary Examiner	
		PREPARED FOR ISSUE	
		Application Examiner	
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